NPN Triple Diffused Planar Silicon Transistor



2SC4108

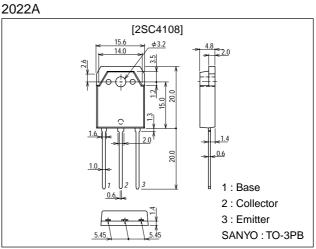
400V/12A Switching Regulator Applications

Features

- \cdot High breakdown voltage and high reliability.
- · Fast switching speed.
- \cdot Wide ASO.
- · Adoption of MBIT process.

Package Dimensions

unit:mm



Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		500	V
Collector-to-Emitter Voltage	VCEO		400	V
Emitter-to-Base Voltage	V _{EBO}		7	V
Collector Current	۱ _C		12	A
Collector Current (Pulse)	ICP	PW≤300µs, duty cycle≤10%	25	A
Base Current	Ι _Β		4	A
Collector Dissipation	PC		2.5	W
		Tc=25°C	100	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	I _{CBO}	V _{CB} =400V, I _E =0			10	μΑ
Emitter Cutoff Current	IEBO	V _{EB} =5V, I _C =0			10	μΑ
	hFE1	V _{CE} =5V, I _C =1.6A	15*		50*	
DC Current Gain	h _{FE} 2	V _{CE} =5V, I _C =8A	10			
	h _{FE} 3	V _{CE} =5V, I _C =10mA	10			

*: The $h_{FE}1$ of the 2SC4108 is classified as follows. When specifying the $h_{FE}1$ rank, specify two ranks or more in principle.

15 L 30 20 M 40 30 N 50

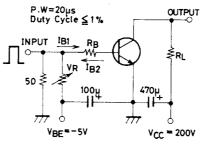
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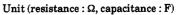
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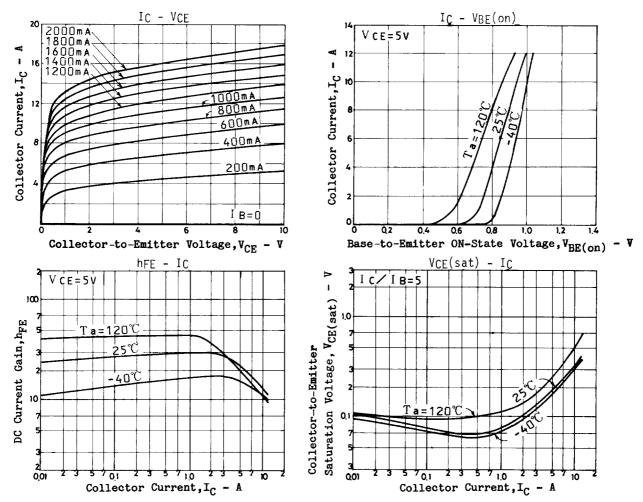
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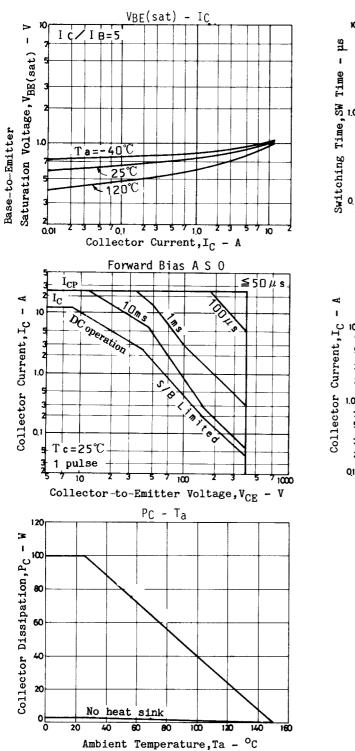
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =8A, I _B =1.6A			0.8	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =8A, I _B =1.6A			1.5	V
Gain-Bandwidth Product	fT	V _{CE} =10V, I _C =1.6A		20		MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		160		pF
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =1mA, I _E =0	500			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =5mA, R _{BE} =∞	400			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	I _E =1mA, I _C =0	7			V
Collector-to-Emitter Sustain Voltage	V _{CEX(sus)}	I _C =6A, I _{B1} =0.6A, I _{B2} =–2.4A, L=500µH, clamped	400			V
Turn-ON Time	ton	I_{C} =10A, I_{B1} =2A, I_{B2} =-4A, R_{L} =20 Ω , V_{CC} =200V			0.5	μs
Storage Time	t _{stg}	I_{C} =10A, I_{B1} =2A, I_{B2} =-4A, R_{L} =20 Ω , V_{CC} =200V			2.5	μs
Fall Time	t _f	I_{C} =10A, I_{B1} =2A, I_{B2} =-4A, R_{L} =20 Ω , V_{CC} =200V			0.3	μs

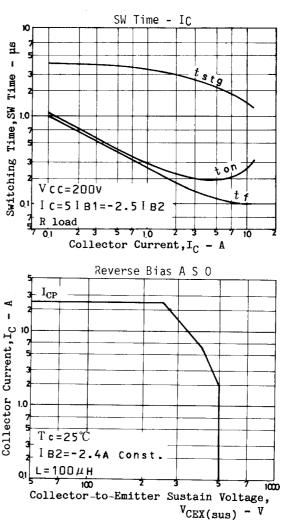
Switching Time Test Circuit











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